# Low Voltage Precision Adjustable Shunt Regulator

# TLV431, NCV431, SCV431

The TLV431A, B and C series are precision low voltage shunt regulators that are programmable over a wide voltage range of 1.24 V to 16 V. The TLV431A series features a guaranteed reference accuracy of  $\pm 1.0\%$  at 25°C and  $\pm 2.0\%$  over the entire industrial temperature range of -40°C to 85°C. The TLV431B series features higher reference accuracy of  $\pm 0.5\%$  and  $\pm 1.0\%$  respectively. For the TLV431C series, the accuracy is even higher. It is  $\pm 0.2\%$  and  $\pm 1.0\%$  respectively. These devices exhibit a sharp low current turn-on characteristic with a low dynamic impedance of 0.20  $\Omega$  over an operating current range of 100  $\mu$ A to 20 mA. This combination of features makes this series an excellent replacement for zener diodes in numerous applications circuits that require a precise reference voltage. When combined with an optocoupler, the TLV431A/B/C can be used as an error amplifier for controlling the feedback loop in isolated low output voltage (3.0 V to 3.3 V) switching power supplies. These devices are available in economical TO-92-3 and micro size TSOP-5 and SOT-23-3 packages.

#### **Features**

- Programmable Output Voltage Range of 1.24 V to 16 V
- Voltage Reference Tolerance ±1.0% for A Series, ±0.5% for B Series and ±0.2% for C Series
- Sharp Low Current Turn-On Characteristic
- Low Dynamic Output Impedance of  $0.20 \Omega$  from  $100 \mu A$  to 20 mA
- Wide Operating Current Range of 50 μA to 20 mA
- Micro Miniature TSOP-5, SOT-23-3 and TO-92-3 Packages
- NCV and SCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

#### **Applications**

- Low Output Voltage (3.0 V to 3.3 V) Switching Power Supply Error Amplifier
- Adjustable Voltage or Current Linear and Switching Power Supplies
- Voltage Monitoring
- Current Source and Sink Circuits
- Analog and Digital Circuits Requiring Precision References
- Low Voltage Zener Diode Replacements

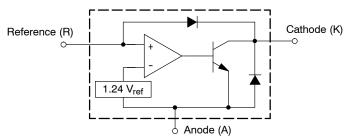
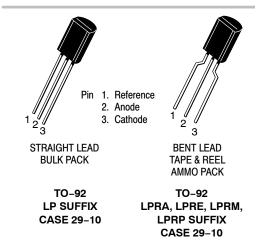


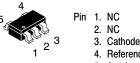
Figure 1. Representative Block Diagram

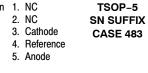


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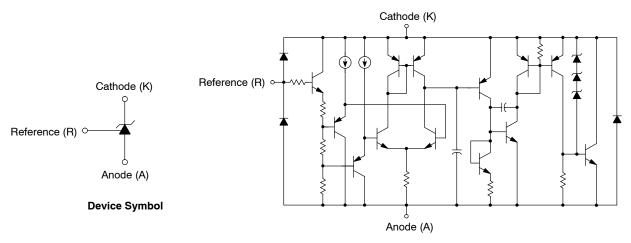
Pin	2.	Reference Cathode Anode	SOT-23 SN1 SUFFIX CASE 318
	J.	Alloue	CAGE 310

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 14 of this data sheet.

# DEVICE MARKING INFORMATION AND PIN CONNECTIONS

See general marking information in the device marking section on page 13 of this data sheet.



The device contains 13 active transistors.

Figure 2. Representative Device Symbol and Schematic Diagram

#### MAXIMUM RATINGS (Full operating ambient temperature range applies, unless otherwise noted)

Rating		Symbol	Value	Unit
Cathode to Anode Voltage		$V_{KA}$	18	V
Cathode Current Range, Continuous		I <sub>K</sub>	-20 to 25	mA
Reference Input Current Range, Continuous		I <sub>ref</sub>	-0.05 to 10	mA
Thermal Characteristics  LP Suffix Package, TO-92-3 Package Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case SN Suffix Package, TSOP-5 Package Thermal Resistance, Junction-to-Ambient SN1 Suffix Package, SOT-23-3 Package Thermal Resistance, Junction-to-Ambient		R <sub>θJA</sub> R <sub>θJC</sub> R <sub>θJA</sub>	178 83 226 491	°C/W
Operating Junction Temperature		T <sub>J</sub>	150	°C
Operating Ambient Temperature Range	TLV431 NCV431, SCV431	T <sub>A</sub>	- 40 to 85 - 40 to 125	°C
Storage Temperature Range		T <sub>stg</sub>	-65 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: This device series contains ESD protection and exceeds the following tests:

Human Body Model 2000 V per JEDEC JESD22-A114F, Machine Model Method 200 V per JEDEC JESD22-A115C,

Charged Device Method 1000 V per JEDEC JESD22-C101E. This device contains latch-up protection and exceeds  $\pm 100$  mA per JEDEC standard JESD78.

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta,JA}}$$

#### RECOMMENDED OPERATING CONDITIONS

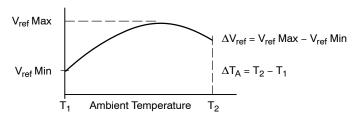
Condition	Symbol	Min	Max	Unit
Cathode to Anode Voltage	V <sub>KA</sub>	V <sub>ref</sub>	16	V
Cathode Current	I <sub>K</sub>	0.1	20	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

		TLV431A		-	TLV431B			
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $ (V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C}) $ $ (T_A = T_{low} \text{ to } T_{high}, \text{ Note 1}) $	V <sub>ref</sub>	1.228 1.215	1.240	1.252 1.265	1.234 1.228	1.240 -	1.246 1.252	٧
Reference Input Voltage Deviation Over Temperature (Figure 3) $(V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_A = T_{low} \text{ to } T_{high}, \text{ Notes } 1, 2, 3)$	$\Delta V_{ref}$	-	7.2	20	-	7.2	20	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to 16 V}, I_{K} = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	-	-0.6	-1.5	-	-0.6	-1.5	mV V
Reference Terminal Current (Figure 4) ( $I_K = 10 \text{ mA}, R1 = 10 \text{ k}\Omega, R2 = \text{open}$ )	I <sub>ref</sub>	-	0.15	0.3	-	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open, Notes 1, 2, 3)	$\Delta I_{ref}$	-	0.04	0.08	-	0.04	0.08	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I <sub>K(min</sub> )	-	30	80	-	30	80	μΑ
Off-State Cathode Current (Figure 5) $(V_{KA} = 6.0 \text{ V}, V_{ref} = 0)$ $(V_{KA} = 16 \text{ V}, V_{ref} = 0)$	I <sub>K(off)</sub>	- -	0.01 0.012	0.04 0.05	- -	0.01 0.012	0.04 0.05	μА
Dynamic Impedance (Figure 3) $(V_{KA} = V_{ref}, I_K = 0.1 \text{ mA to } 20 \text{ mA, } f \le 1.0 \text{ kHz, Note 4})$	Z <sub>KA</sub>	-	0.25	0.4	-	0.25	0.4	Ω

- 1. Ambient temperature range:  $T_{low} = -40^{\circ}C$ ,  $T_{high} = 85^{\circ}C$ . 2. Guaranteed but not tested.
- 3. The deviation parameters  $\Delta V_{ref}$  and  $\Delta I_{ref}$  are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage,  $\alpha V_{\text{ref}}$  is defined as:

$$\alpha V_{ref} \left( \frac{ppm}{{}^{\circ}C} \right) = \frac{\left( \frac{(\Delta V_{ref})}{V_{ref} \left( T_{A} = 25 {}^{\circ}C \right)} \times 10^{6} \right)}{\Delta T_{A}}$$

αV<sub>ref</sub> can be positive or negative depending on whether V<sub>ref</sub> Min or V<sub>ref</sub> Max occurs at the lower ambient temperature, refer to Figure 8. Example:  $\Delta V_{ref} = 7.2 \text{ mV}$  and the slope is positive,

$$V_{ref}$$
 @ 25°C = 1.241 V  $\Delta T_A$  = 125°C

$$\alpha V_{ref} \left( \frac{ppm}{{}^{\circ}C} \right) = \frac{0.0072}{1.241} \times 10^{6} = 46 \text{ ppm/}^{\circ}C$$

4. The dynamic impedance  $Z_{\mbox{\scriptsize KA}}$  is defined as:

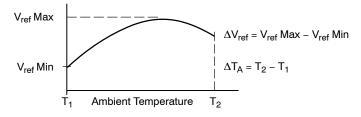
$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

$$|Z_{KA}'| = |Z_{KA}| \times \left(1 + \frac{R1}{R2}\right)$$

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

		TLV431C			
Characteristic	Symbol	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $ (V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C}) $ $ (T_A = T_{low} \text{ to } T_{high}, \text{ Note 5}) $	V <sub>ref</sub>	1.237 1.228	1.240	1.243 1.252	V
Reference Input Voltage Deviation Over Temperature (Figure 3) $(V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = T_{low} \text{ to } T_{high}, \text{ Notes 5, 6, 7)}$	$\Delta V_{ref}$	-	7.2	20	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to } 16 \text{ V}, I_K = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	-	-0.6	-1.5	mV V
Reference Terminal Current (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open)	I <sub>ref</sub>	-	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open, Notes 5, 6, 7)	$\Delta I_{ref}$	-	0.04	0.08	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I <sub>K(min</sub> )	-	30	80	μΑ
Off-State Cathode Current (Figure 5) (V <sub>KA</sub> = 6.0 V, V <sub>ref</sub> = 0) (V <sub>KA</sub> = 16 V, V <sub>ref</sub> = 0)	I <sub>K(off)</sub>		0.01 0.012	0.04 0.05	μΑ
Dynamic Impedance (Figure 3) $ (V_{KA} = V_{ref}, I_K = 0.1 \text{ mA to } 20 \text{ mA, } f \leq 1.0 \text{ kHz, Note 8} ) $	Z <sub>KA</sub>	_	0.25	0.4	Ω

- 5. Ambient temperature range:  $T_{low} = -40^{\circ}C$ ,  $T_{high} = 85^{\circ}C$ . 6. Guaranteed but not tested.
- The deviation parameters  $\Delta V_{ref}$  and  $\Delta I_{ref}$  are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage,  $\alpha V_{ref}$  is defined as:

$$\alpha V_{ref} \, \left( \frac{ppm}{^{\circ}C} \right) = \frac{\left( \frac{(\Delta V_{ref})}{V_{ref} \, \left( T_{A} = 25^{\circ}C \right)} \times \, 10^{6} \right)}{\Delta T_{A}}$$

 $\alpha V_{ref}$  can be positive or negative depending on whether  $V_{ref}$  Min or  $V_{ref}$  Max occurs at the lower ambient temperature, refer to Figure 8. Example:  $\Delta V_{ref} = 7.2 \text{ mV}$  and the slope is positive,

$$V_{ref}$$
 @ 25°C = 1.241 V  $\Delta T_A$  = 125°C

$$\alpha V_{ref} \left( \frac{ppm}{{}^{\circ}C} \right) = \frac{\frac{0.0072}{1.241} \times 10^{6}}{125} = 46 \text{ ppm}/{}^{\circ}C$$

8. The dynamic impedance Z<sub>KA</sub> is defined as:

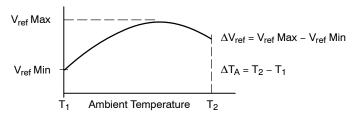
$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted. NCV prefix indicates TSOP package device. SCV prefix indicates SOT–23 package device.)

		NCV4	31A, SC	V431A	
Characteristic	Symbol	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $ (V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C}) $ $ (T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}) $ $ (T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}) $	V <sub>ref</sub>	1.228 1.215 1.211	1.240 - -	1.252 1.265 1.265	٧
Reference Input Voltage Deviation Over Temperature (Figure 3) $ (V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C}, \text{ Notes } 9, 10) \\ (V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_{A} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \text{ Notes } 9, 10) $	$\Delta V_{ref}$	<u>-</u>	7.2 7.2	20 24	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to 16 V}, I_{K} = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	_	-0.6	-1.5	$\frac{mV}{V}$
Reference Terminal Current (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open)	I <sub>ref</sub>	_	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open, T <sub>A</sub> = $-40^{\circ}$ C to 85°C, Notes 9, 10) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open, T <sub>A</sub> = $-40^{\circ}$ C to 125°C, Notes 9, 10)	$\Delta I_{ref}$	<u>-</u>	0.04	0.08 0.10	μА
Minimum Cathode Current for Regulation (Figure 3)	I <sub>K(min</sub> )	_	30	80	μΑ
Off-State Cathode Current (Figure 5) $(V_{KA} = 6.0 \text{ V}, V_{ref} = 0)$ $(V_{KA} = 16 \text{ V}, V_{ref} = 0)$	I <sub>K(off)</sub>	- -	0.01 0.012	0.04 0.05	μА
Dynamic Impedance (Figure 3) $(V_{KA}=V_{ref},I_{K}=0.1\text{mA}\text{to}20\text{mA},f\leq1.0\text{kHz},\text{Note}11)$	Z <sub>KA</sub>	-	0.25	0.4	Ω

<sup>9.</sup> Guaranteed but not tested.

<sup>10.</sup> The deviation parameters  $\Delta V_{ref}$  and  $\Delta I_{ref}$  are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage,  $\alpha \text{V}_{\text{ref}}$  is defined as:

$$\alpha V_{ref} \left( \frac{ppm}{^{\circ}C} \right) = \frac{\left( \frac{(\Delta V_{ref})}{V_{ref} \left( T_{A} = 25^{\circ}C \right)} \times 10^{6} \right)}{\Delta T_{\Delta}}$$

 $\alpha V_{ref}$  can be positive or negative depending on whether  $V_{ref}$  Min or  $V_{ref}$  Max occurs at the lower ambient temperature, refer to Figure 8.

Example:  $\Delta V_{ref}$  = 7.2 mV and the slope is positive,

$$V_{ref}$$
 @ 25°C = 1.241 V  $\Delta T_A$  = 125°C

$$\alpha V_{\mbox{ref}} \left( \frac{\mbox{ppm}}{^{\circ}\mbox{C}} \right) = \frac{0.0072}{1.241} \times 10^{6} \\ = 46 \ \mbox{ppm}/^{\circ}\mbox{C}$$

11. The dynamic impedance  $Z_{KA}$  is defined as:

$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

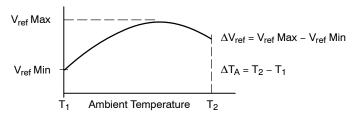
$$|Z_{KA}'| = |Z_{KA}| \times \left(1 + \frac{R1}{R2}\right)$$

ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted. NCV prefix indicates TSOP package device. SCV prefix indicates SOT-23 package device.)

Characteristic	Symbol	Min	Тур	Max	Unit
Reference Voltage (Figure 3) $ (V_{KA} = V_{ref}, I_K = 10 \text{ mA}, T_A = 25^{\circ}\text{C}) $ $ (T_A = -40^{\circ}\text{C to }85^{\circ}\text{C}) $ $ (T_A = -40^{\circ}\text{C to }125^{\circ}\text{C}) $	V <sub>ref</sub>	1.234 1.228 1.224	1.240 - -	1.246 1.252 1.252	V
Reference Input Voltage Deviation Over Temperature (Figure 3) $(V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_A = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C}, \text{ Notes } 9, 10)$ $(V_{KA} = V_{ref}, I_{K} = 10 \text{ mA}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}, \text{ Notes } 9, 10)$	$\Delta V_{ref}$	<u>-</u>	7.2 7.2	20 24	mV
Ration of Reference Input Voltage Change to Cathode Voltage Change (Figure 4) $(V_{KA} = V_{ref} \text{ to 16 V}, I_{K} = 10 \text{ mA})$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	_	-0.6	-1.5	mV V
Reference Terminal Current (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open)	I <sub>ref</sub>	-	0.15	0.3	μΑ
Reference Input Current Deviation Over Temperature (Figure 4) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open, T <sub>A</sub> = $-40^{\circ}$ C to 85°C, Notes 12, 13) (I <sub>K</sub> = 10 mA, R1 = 10 k $\Omega$ , R2 = open, T <sub>A</sub> = $-40^{\circ}$ C to 125°C, Notes 12, 13)	$\Delta I_{ref}$	<u>-</u>	0.04	0.08 0.10	μΑ
Minimum Cathode Current for Regulation (Figure 3)	I <sub>K(min</sub> )	_	30	80	μΑ
Off-State Cathode Current (Figure 5) $(V_{KA} = 6.0 \text{ V}, V_{ref} = 0)$ $(V_{KA} = 16 \text{ V}, V_{ref} = 0)$	I <sub>K(off)</sub>	<u>-</u>	0.01 0.012	0.04 0.05	μΑ
Dynamic Impedance (Figure 3) $(V_{KA} = V_{ref}, I_K = 0.1 \text{ mA to } 20 \text{ mA, } f \leq 1.0 \text{ kHz, Note } 14)$	Z <sub>KA</sub>	_	0.25	0.4	Ω

<sup>12.</sup> Guaranteed but not tested.

<sup>13.</sup> The deviation parameters  $\Delta V_{ref}$  and  $\Delta I_{ref}$  are defined as the difference between the maximum value and minimum value obtained over the full operating ambient temperature range that applied.



The average temperature coefficient of the reference input voltage,  $\alpha V_{ref}$  is defined as:

$$\alpha V_{ref} \left( \frac{ppm}{^{\circ}C} \right) = \frac{\left( \frac{(\Delta V_{ref})}{V_{ref} (T_{A} = 25^{\circ}C)} \times 10^{6} \right)}{\Delta T_{A}}$$

 $\alpha V_{ref}$  can be positive or negative depending on whether  $V_{ref}$  Min or  $V_{ref}$  Max occurs at the lower ambient temperature, refer to Figure 8.

Example:  $\Delta V_{ref}$  = 7.2 mV and the slope is positive,  $V_{ref}$  @ 25°C = 1.241 V  $\Delta T_A$  = 125°C

$$\alpha V_{ref} \left( \frac{ppm}{^{\circ}C} \right) = \frac{0.0072 \times 10^{6}}{1.241} = 46 \; ppm/^{\circ}C$$

14. The dynamic impedance  $Z_{\mbox{\scriptsize KA}}$  is defined as:

$$|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

$$|Z_{KA}'| = |Z_{KA}| \times \left(1 + \frac{R1}{R2}\right)$$

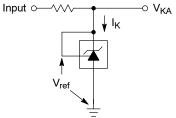


Figure 3. Test Circuit

for  $V_{KA} = V_{ref}$ 

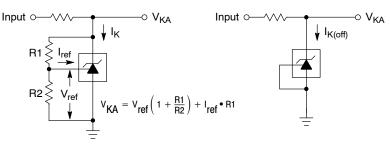


Figure 4. Test Circuit for  $V_{KA} > V_{ref}$ 

Figure 5. Test Circuit for I<sub>K(off)</sub>

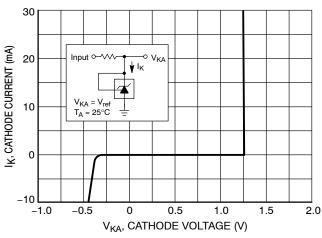


Figure 6. Cathode Current vs. Cathode Voltage

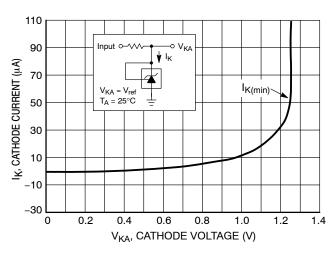


Figure 7. Cathode Current vs. Cathode Voltage

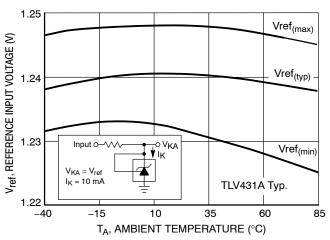


Figure 8. Reference Input Voltage versus **Ambient Temperature** 

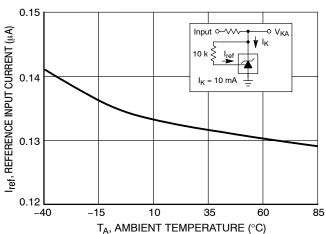
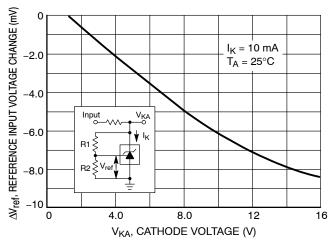


Figure 9. Reference Input Current versus **Ambient Temperature** 

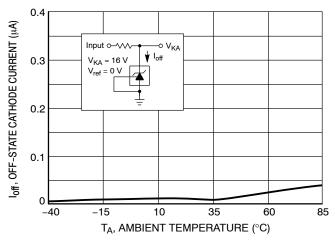


4.0

(Val = 16 V Vref = 0 V Vref

Figure 10. Reference Input Voltage Change versus Cathode Voltage

Figure 11. Off-State Cathode Current versus Cathode Voltage



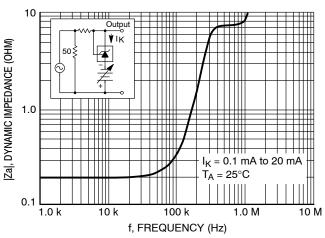
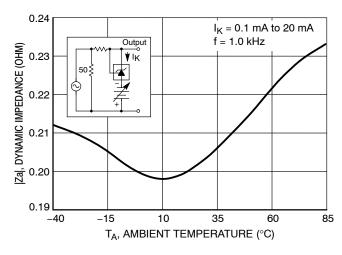


Figure 12. Off-State Cathode Current versus
Ambient Temperature

Figure 13. Dynamic Impedance versus Frequency



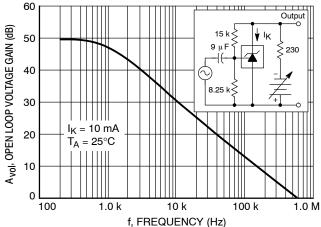
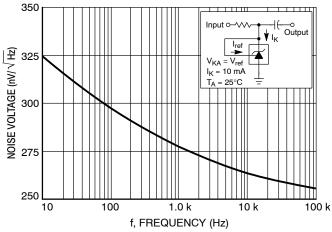


Figure 14. Dynamic Impedance versus

Ambient Temperature

Figure 15. Open-Loop Voltage Gain versus Frequency

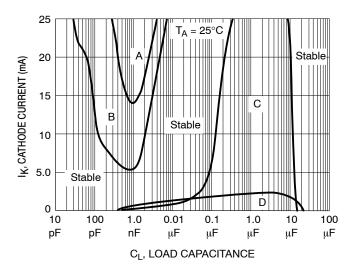


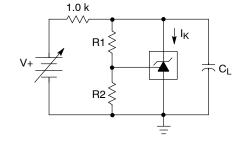
0 2.0 3.0 1.0 4.0

1.8 kΩ Output Generator = 100 kHz 1.5 Output 1.0 (VOLTS) T<sub>A</sub> = 25°C 0.5 Input 0 2.0 5.0 6.0 7.0 8.0 9.0 t, TIME (μs)

Figure 16. Spectral Noise Density

Figure 17. Pulse Response





V<sub>KA</sub> (V) Unstable R1 R2 Regions  $(k\Omega)$  $(k\Omega)$ A, C 0  $V_{ref}$ ∞ B, D 5.0 30.4 10

Figure 18. Stability Boundary Conditions

Figure 19. Test Circuit for Figure 18

# Stability

Figures 18 and 19 show the stability boundaries and circuit configurations for the worst case conditions with the load capacitance mounted as close as possible to the device. The required load capacitance for stable operation can vary depending on the operating temperature and capacitor

equivalent series resistance (ESR). Ceramic or tantalum surface mount capacitors are recommended for both temperature and ESR. The application circuit stability should be verified over the anticipated operating current and temperature ranges.

# **TYPICAL APPLICATIONS**

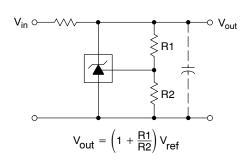


Figure 20. Shunt Regulator

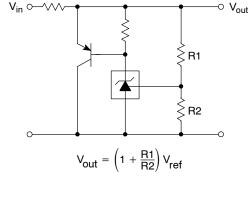


Figure 21. High Current Shunt Regulator

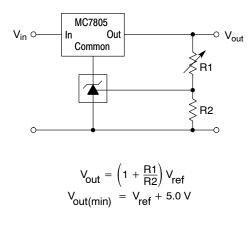


Figure 22. Output Control for a Three Terminal Fixed Regulator

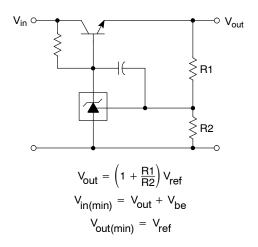


Figure 23. Series Pass Regulator

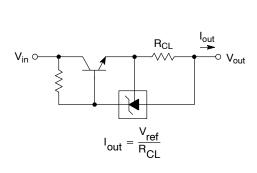


Figure 24. Constant Current Source

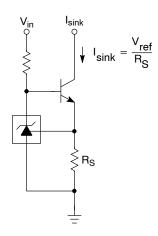


Figure 25. Constant Current Sink

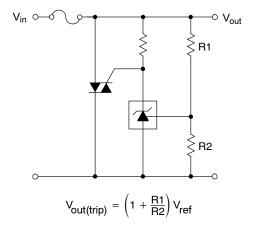


Figure 26. TRIAC Crowbar

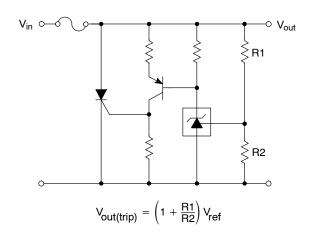
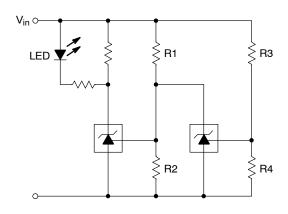


Figure 27. SCR Crowbar



 $\label{eq:L.E.D.} \text{L.E.D. indicator is 'ON' when } V_{in} \text{ is between the upper and lower limits,}$ 

Lower limit = 
$$\left(1 + \frac{R1}{R2}\right) V_{ref}$$
  
Upper limit =  $\left(1 + \frac{R3}{R4}\right) V_{ref}$ 

Figure 28. Voltage Monitor

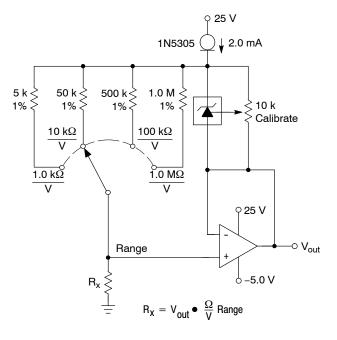


Figure 29. Linear Ohmmeter

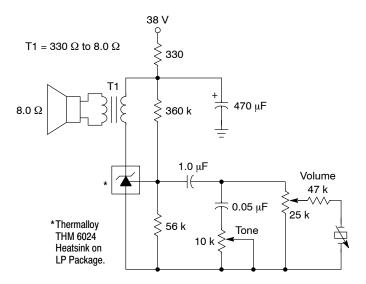


Figure 30. Simple 400 mW Phono Amplifier

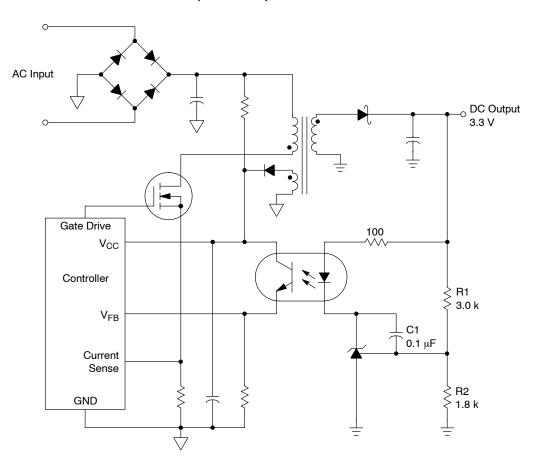
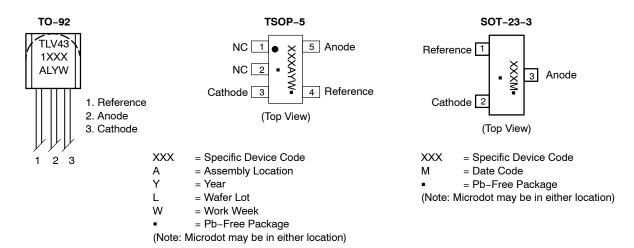


Figure 31. Isolated Output Line Powered Switching Power Supply

The above circuit shows the TLV431A/B/C as a compensated amplifier controlling the feedback loop of an isolated output line powered switching regulator. The output voltage is programmed to 3.3 V by the resistors values selected for R1 and R2. The minimum output voltage that can be programmed with this circuit is 2.64 V, and is limited by the sum of the reference voltage (1.24 V) and the forward drop of the optocoupler light emitting diode (1.4 V). Capacitor C1 provides loop compensation.

#### PIN CONNECTIONS AND DEVICE MARKING

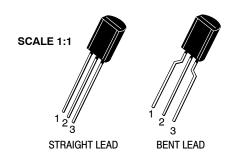


#### **ORDERING INFORMATION**

Device	Device Code	Package	Shipping <sup>†</sup>
TLV431ALPG	ALP	TO-92-3 (Pb-Free)	6000 / Box
TLV431ALPRAG	ALP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431ALPREG	ALP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431ALPRMG	ALP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431ALPRPG	ALP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431ASNT1G	RAA	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431ASN1T1G	RAF	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431BLPG	BLP	TO-92-3 (Pb-Free)	6000 / Box
TLV431BLPRAG	BLP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431BLPREG	BLP	TO-92-3 (Pb-Free)	2000 / Tape & Reel
TLV431BLPRMG	BLP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431BLPRPG	BLP	TO-92-3 (Pb-Free)	2000 / Ammo Pack
TLV431BSNT1G	RAH	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431BSN1T1G	RAG	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
TLV431CSN1T1G	AAN	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
SCV431ASN1T1G*	RAE	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
SCV431BSN1T1G*	RAC	SOT-23-3 (Pb-Free, Halide-Free)	3000 / Tape & Reel
NCV431ASNT1G*	ACH	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel
NCV431BSNT1G*	AD6	TSOP-5 (Pb-Free, Halide-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*SCV, NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and

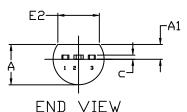
PPAP Capable.

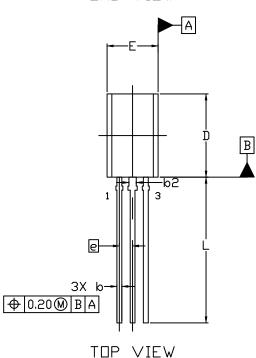


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

#### STRAIGHT LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Δ	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
Ø	0.38	0.465	0.55		
ρQ	0.62	0.70	0.78		
C	0.35	0.40	0.45		
D	7.85	8.00	8.15		
E	4.75	4.90	5.05		
E2	3.90				
е	1.27 BSC				
L	13.80	14.00	14.20		

#### STYLES AND MARKING ON PAGE 3

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DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 1 OF 3	

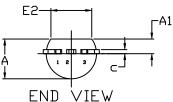
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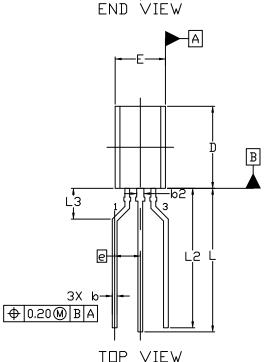


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

#### FORMED LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS					
DIM	MIN.	N□M.	MAX.			
Α	3.75	3.90	4.05			
A1	1.28	1.43	1.58			
b	0.38	0.465	0.55			
b2	0.62	0.70	0.78			
С	0.35	0.40	0.45			
D	7.85	8.00	8.15			
Е	4.75	4.90	5.05			
E2	3.90					
O.		2.50 BSC				
L	13.80	14.00	14.20			
L2	13.20	13.60	14.00			
L3	·	3.00 REF				

#### **STYLES AND MARKING ON PAGE 3**

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# TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

#### **DATE 05 MAR 2021**

2.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	
	GATE	PIN 1.	SOURCE DRAIN	PIN 1. 2.	DRAIN	2.	BASE 1 EMITTER BASE 2		CATHODE GATE ANODE
2.	CATHODE & ANODE	2.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	2.	ANODE 1 GATE CATHODE 2		EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1
2.	ANODE	DINI 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	PIN 1. 2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.		PIN 1. 2.		PIN 1. 2.	GATE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
	V <sub>CC</sub>		MT	PIN 1. 2.		PIN 1. 2.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

# GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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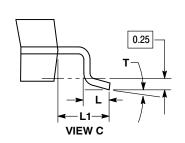


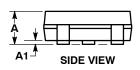
SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

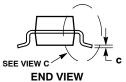
**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

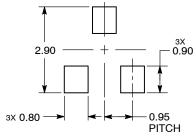
**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

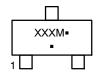
3. ANODE

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	PIN 1. CATHODE 2. CATHODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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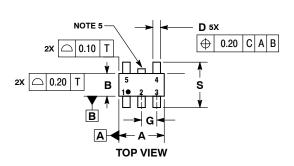
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3. CATHODE

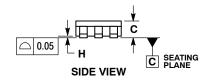


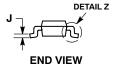
TSOP-5 **CASE 483 ISSUE N** 

**DATE 12 AUG 2020** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE
  MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.85	3.15		
В	1.35	1.65		
C	0.90	1.10		
D	0.25	0.50		
G	0.95 BSC			
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
М	0 °	10 °		
S	2 50	3.00		

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location = Date Code = Year = Pb-Free Package

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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onsemi Website: www.onsemi.com

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Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative